Preferred Device

# Sensitive Gate Silicon Controlled Rectifiers

## **Reverse Blocking Thyristors**

PNPN devices designed for high volume, line-powered consumer applications such as relay and lamp drivers, small motor controls, gate drivers for larger thyristors, and sensing and detection circuits. Supplied in an inexpensive plastic TO-226AA package which is readily adaptable for use in automatic insertion equipment.

- Sensitive Gate Allows Triggering by Microcontrollers and Other Logic Circuits
- Blocking Voltage to 600 Volts
- On–State Current Rating of 0.8 Amperes RMS at 80°C
- High Surge Current Capability 10 Amperes
- Minimum and Maximum Values of IGT, VGT and IH Specified for Ease of Design
- Immunity to dV/dt 20 V/μsec Minimum at 110°C
- Glass-Passivated Surface for Reliability and Uniformity
- Device Marking: Device Type, e.g., MCR100-3, Date Code

#### MAXIMUM RATINGS (T<sub>J</sub> = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
Peak Repetitive Off–State Voltage <sup>(1)</sup> (T <sub>J</sub> = -40 to 110°C, Sine Wave, 50 to 60 Hz; Gate Open)  MCR100-3  MCR100-4  MCR100-6  MCR100-8	VDRM, VRRM	100 200 400 600	Volts
On-State RMS Current (T <sub>C</sub> = 80°C) 180° Conduction Angles	IT(RMS)	0.8	Amp
Peak Non-Repetitive Surge Current (1/2 Cycle, Sine Wave, 60 Hz, T <sub>J</sub> = 25°C)	ITSM	10	Amps
Circuit Fusing Consideration (t = 8.3 ms)	l <sup>2</sup> t	0.415	A <sup>2</sup> s
Forward Peak Gate Power (T <sub>A</sub> = 25°C, Pulse Width ≤ 1.0 μs)	PGM	0.1	Watt
Forward Average Gate Power (T <sub>A</sub> = 25°C, t = 8.3 ms)	PG(AV)	0.10	Watt
Forward Peak Gate Current (Τ <sub>A</sub> = 25°C, Pulse Width ≤ 1.0 μs)	IGM	1.0	Amp
Reverse Peak Gate Voltage $(T_A = 25^{\circ}C, \text{ Pulse Width } \leq 1.0 \mu\text{s})$	VGRM	5.0	Volts
Operating Junction Temperature Range  @ Rate V <sub>RRM</sub> and V <sub>DRM</sub>	TJ	–40 to 110	°C
Storage Temperature Range	T <sub>stg</sub>	–40 to 150	°C

(1) VDRM and VRRM for all types can be applied on a continuous basis. Ratings apply for zero or negative gate voltage; however, positive gate voltage shall not be applied concurrent with negative potential on the anode. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.



#### ON Semiconductor

http://onsemi.com

## SCRs 0.8 AMPERES RMS 100 thru 600 VOLTS





TO-92 (TO-226AA) CASE 029 STYLE 10

PIN ASSIGNMENT			
1 Cathode			
2	Gate		
3	Anode		

#### ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 6 of this data sheet.

**Preferred** devices are recommended choices for future use and best overall value.

#### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance — Junction to Case — Junction to Ambient	R <sub>θJC</sub> R <sub>θJA</sub>	75 200	°C/W
Lead Solder Temperature (<1/16" from case, 10 secs max)	TL	260	°C

#### **ELECTRICAL CHARACTERISTICS** (T<sub>C</sub> = 25°C unless otherwise noted)

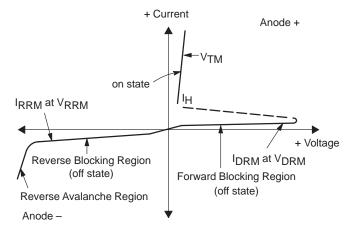
Characteristic	Symbol	Min	Тур	Max	Unit	
DFF CHARACTERISTICS						
Peak Repetitive Forward or Reverse Blocking Current <sup>(1)</sup> ( $V_D$ = Rated $V_{DRM}$ and $V_{RRM}$ ; $R_{GK}$ = 1 $k\Omega$ )	T <sub>C</sub> = 25°C T <sub>C</sub> = 110°C	I <sub>DRM</sub> , I <sub>RRM</sub>	_ _	_	10 100	μА
ON CHARACTERISTICS						
Peak Forward On–State Voltage(*) (I <sub>TM</sub> = 1.0 Amp Peak @ T <sub>A</sub> = 25°C)		V <sub>TM</sub>	_	_	1.7	Volts
Gate Trigger Current (Continuous dc) <sup>(2)</sup> (V <sub>AK</sub> = 7.0 Vdc, R <sub>L</sub> = 100 Ohms)	T <sub>C</sub> = 25°C	IGT	_	40	200	μΑ
Holding Current(2) (VAK = 7.0 Vdc, Initiating Current = 20 mA)	$T_C = 25^{\circ}C$ $T_C = -40^{\circ}C$	lн	_	0.5 —	5.0 10	mA
Latch Current $(V_{AK} = 7.0 \text{ V}, \text{ Ig} = 200 \mu\text{A})$	$T_C = 25^{\circ}C$ $T_C = -40^{\circ}C$	l∟	_	0.6 —	10 15	mA
Gate Trigger Voltage (Continuous dc) <sup>(2)</sup> (V <sub>AK</sub> = 7.0 Vdc, R <sub>L</sub> = 100 Ohms) T <sub>C</sub> = -40°C	T <sub>C</sub> = 25°C	VGT	_ _	0.62 —	0.8 1.2	Volts
DYNAMIC CHARACTERISTICS						
Critical Rate of Rise of Off–State Voltage ( $V_D$ = Rated $V_{DRM}$ , Exponential Waveform, $R_{GK}$ = 1000 Ohms, $T_J$ = 110°C)		dV/dt	20	35	_	V/µs
Critical Rate of Rise of On–State Current (IpK = 20 A; Pw = 10 µsec; diG/dt = 1 A/µsec, Igt = 20 mA)		di/dt	_	_	50	A/μs

<sup>\*</sup>Indicates Pulse Test: Pulse Width ≤ 1.0 ms, Duty Cycle ≤ 1%.

<sup>(1)</sup>  $R_{GK}$  = 1000 Ohms included in measurement. (2) Does not include  $R_{GK}$  in measurement.

### **Voltage Current Characteristic of SCR**

Symbol	Parameter
VDRM	Peak Repetitive Off State Forward Voltage
IDRM	Peak Forward Blocking Current
VRRM	Peak Repetitive Off State Reverse Voltage
I <sub>RRM</sub>	Peak Reverse Blocking Current
$V_{TM}$	Peak on State Voltage
lμ	Holding Current



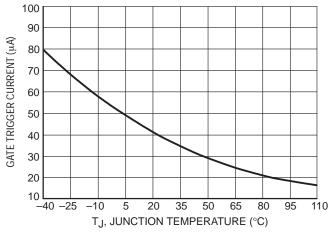


Figure 1. Typical Gate Trigger Current versus Junction Temperature

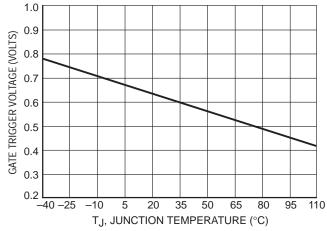
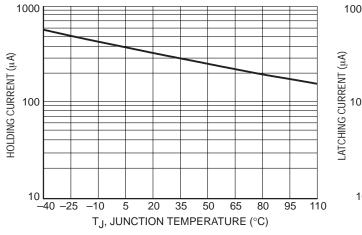


Figure 2. Typical Gate Trigger Voltage versus
Junction Temperature

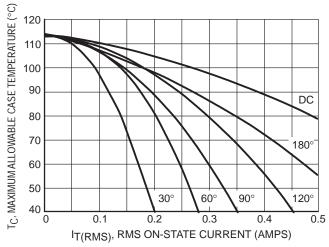
10



1000 <del>-40 -25 -10</del> 20 50 80 95 110 5 35 65 T<sub>.J</sub>, JUNCTION TEMPERATURE (°C)

Figure 3. Typical Holding Current versus Junction Temperature

Figure 4. Typical Latching Current versus **Junction Temperature** 



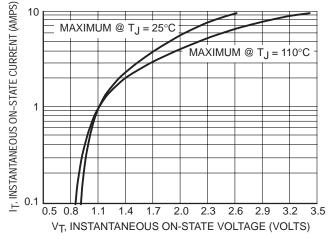


Figure 5. Typical RMS Current Derating

Figure 6. Typical On-State Characteristics

#### TO-92 EIA RADIAL TAPE IN FAN FOLD BOX OR ON REEL

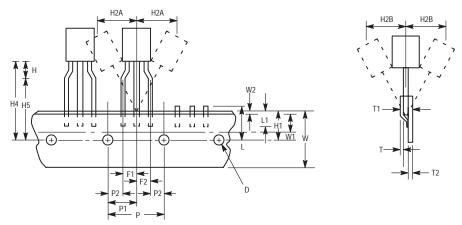


Figure 7. Device Positioning on Tape

			Specification			
		Inc	hes	Millir	neter	
Symbol	Item	Min	Max	Min	Max	
D	Tape Feedhole Diameter	0.1496	0.1653	3.8	4.2	
D2	Component Lead Thickness Dimension	0.015	0.020	0.38	0.51	
F1, F2	Component Lead Pitch	0.0945	0.110	2.4	2.8	
Н	Bottom of Component to Seating Plane	.059	.156	1.5	4.0	
H1	Feedhole Location	0.3346	0.3741	8.5	9.5	
H2A	Deflection Left or Right	0	0.039	0	1.0	
H2B	Deflection Front or Rear	0	0.051	0	1.0	
H4	Feedhole to Bottom of Component	0.7086	0.768	18	19.5	
H5	Feedhole to Seating Plane	0.610	0.649	15.5	16.5	
L	Defective Unit Clipped Dimension	0.3346	0.433	8.5	11	
L1	Lead Wire Enclosure	0.09842	_	2.5	_	
Р	Feedhole Pitch	0.4921	0.5079	12.5	12.9	
P1	Feedhole Center to Center Lead	0.2342	0.2658	5.95	6.75	
P2	First Lead Spacing Dimension	0.1397	0.1556	3.55	3.95	
Т	Adhesive Tape Thickness	0.06	0.08	0.15	0.20	
T1	Overall Taped Package Thickness	_	0.0567	_	1.44	
T2	Carrier Strip Thickness	0.014	0.027	0.35	0.65	
W	Carrier Strip Width	0.6889	0.7481	17.5	19	
W1	Adhesive Tape Width	0.2165	0.2841	5.5	6.3	
W2	Adhesive Tape Position	.0059	0.01968	.15	0.5	

#### NOTES:

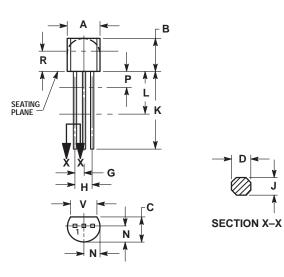
- 1. Maximum alignment deviation between leads not to be greater than 0.2 mm.
- 2. Defective components shall be clipped from the carrier tape such that the remaining protrusion (L) does not exceed a maximum of 11 mm.
- 3. Component lead to tape adhesion must meet the pull test requirements.
- 4. Maximum non-cumulative variation between tape feed holes shall not exceed 1 mm in 20 pitches.
- 5. Holddown tape not to extend beyond the edge(s) of carrier tape and there shall be no exposure of adhesive.
- 6. No more than 1 consecutive missing component is permitted.
- 7. A tape trailer and leader, having at least three feed holes is required before the first and after the last component.
- 8. Splices will not interfere with the sprocket feed holes.

## ORDERING & SHIPPING INFORMATION: MCR100 Series packaging options, Device Suffix

U.S.	Europe Equivalent	Shipping	Description of TO92 Tape Orientation
MCR100-3,4,6,8 MCR100-6RLRA MCR100-6RLRM	MCR100-3RL,6RL,8RL MCR100-6ZL1	Bulk in Box (5K/Box) Radial Tape and Reel (2K/Reel) Radial Tape and Fan Fold Box (2K/Box)	N/A, Bulk Round side of TO92 and adhesive tape visible Flat side of TO92 and adhesive tape visible

#### **PACKAGE DIMENSIONS**

#### TO-92 (TO-226AA) CASE 029-11 **ISSUE AJ**



- NOTES:
  1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
  2. CONTROLLING DIMENSION: INCH.
  3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
  4. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	INCHES		MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.175	0.205	4.45	5.20
В	0.170	0.210	4.32	5.33
С	0.125	0.165	3.18	4.19
D	0.016	0.021	0.407	0.533
G	0.045	0.055	1.15	1.39
Н	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
K	0.500		12.70	
L	0.250		6.35	
N	0.080	0.105	2.04	2.66
Р		0.100		2.54
R	0.115		2.93	
٧	0.135		3.43	

STYLE 10: PIN 1. CATHODE 2. GATE 3. ANODE

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